

## Silicon PNP Power Transistors

## 2N6296 2N6297

**DESCRIPTION**

- With TO-66 package
- DARLINGTON
- Complement to type 2N6294/6295

**APPLICATIONS**

- For high gain amplifier and medium speed switching applications

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

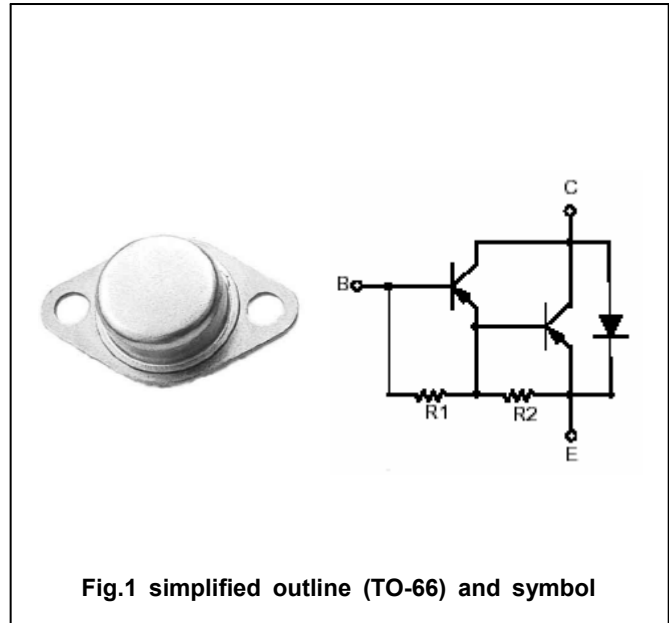


Fig.1 simplified outline (TO-66) and symbol

**Absolute maximum ratings(Ta=25□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2N6296	-60	V
		2N6297	-80	
V <sub>CEO</sub>	Collector-emitter voltage	2N6296	-60	V
		2N6298	-80	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-4	A
I <sub>CM</sub>	Collector current-Peak		-8	A
I <sub>B</sub>	Base current		-80	mA
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25□	50	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-65~200	□

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	3.5	□/W

## Silicon PNP Power Transistors

## 2N6296 2N6297

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA ; I <sub>B</sub> =0	-60			V
			-80			
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A ; I <sub>B</sub> =-8mA			-2.0	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-40mA			-3.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-40mA			-4.0	V
V <sub>BE</sub>	Base -emitter on voltage	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-3V			-2.8	V
I <sub>CEX</sub>	Collector cut-off current	V <sub>CE</sub> =Rated V <sub>CE</sub> ; V <sub>BE(off)</sub> =1.5V T <sub>C</sub> =150 °C			-0.5 -5.0	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =1/2Rated V <sub>CEO</sub> ; I <sub>B</sub> =0			-0.5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-2.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-3V	750		18000	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-3V	100			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1.5A ; V <sub>CE</sub> =-3V; f=1.0MHz	4.0			MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=0.1MHz			200	pF

Silicon PNP Power Transistors

2N6296 2N6297

PACKAGE OUTLINE



Fig.2 Outline dimensions

Silicon PNP Power Transistors

2N6296 2N6297

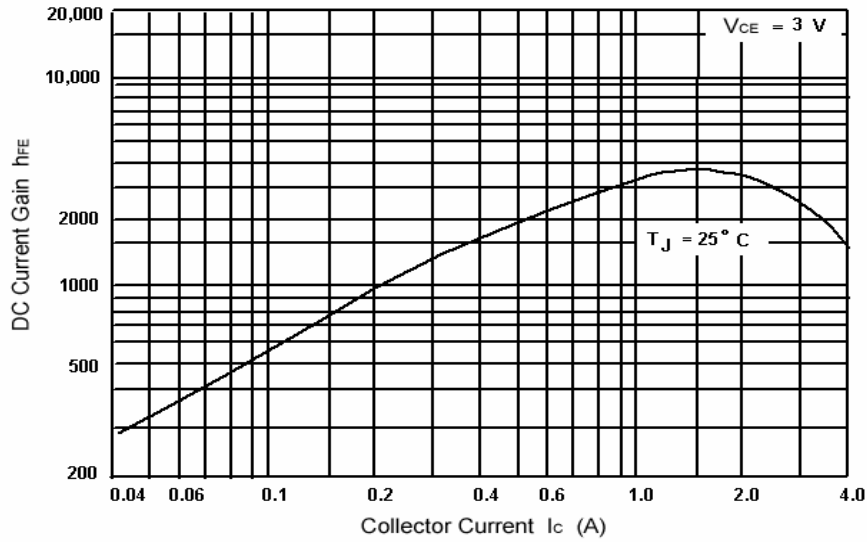


Fig.3 DC current Gain

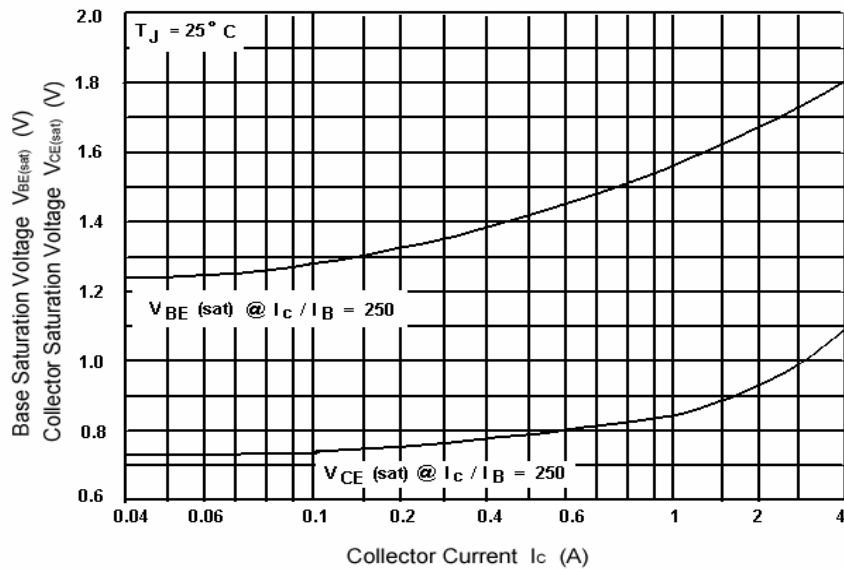


Fig.4 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

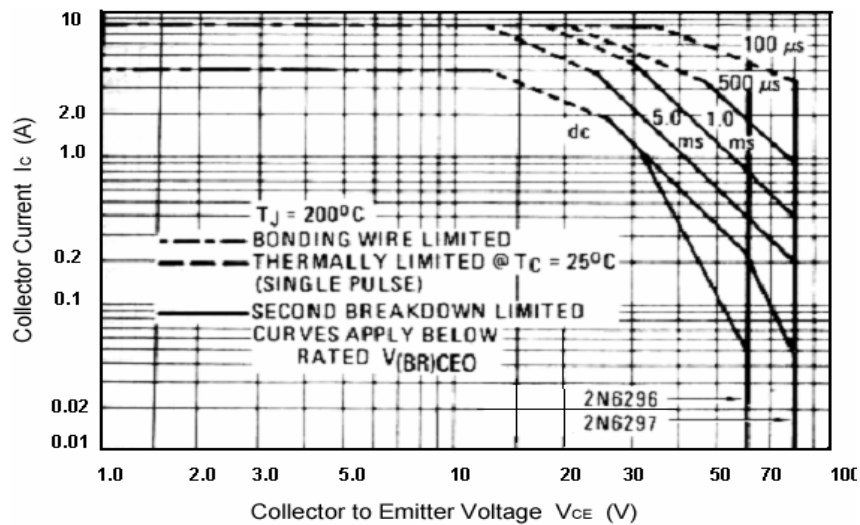


Fig.5 Safe Operating Area